NSN 5961-01-107-8665

Thyristor Semiconductor Device - Page 1 of 1

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Inclosure Material:

Metal

Overall Length:

1.140 inches

Mounting Facility Quantity:

1

Internal Configuration:

Junction contact

Mounting Method:

Threaded stud

Features Provided:

Hermetically sealed case

Overall Width Across Flats:

1.063 inches

Thread Size:

0.500 inches

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

900.0 repetitive peak reverse voltage, peak total value, gate terminal open-circuited

Current Rating Per Characteristic:

110.00 amperes forward current, total rms horsepower metric

Power Rating Per Characteristic:

5.0 watts small-signal input power, common-collector blank

Maximum Operating Tempurature Per Measurement Point:

125.0 degrees celsius junction

Special Features:

Junction pattern arrangement: pnpn

Thread Series Designator:

Unf

Terminal Type And Quantity:

1 threaded stud and 3 tab, solder lug

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0